OM SENI

AOD600A70

700V, aMOS5™ N-Channel Power Transistor

General Description

- Proprietary αMOS5™ technology
- Low $R_{DS(ON)}$
- Optimized switching parameters for better EMI performance
- Enhanced body diode for robustness and fast reverse recovery

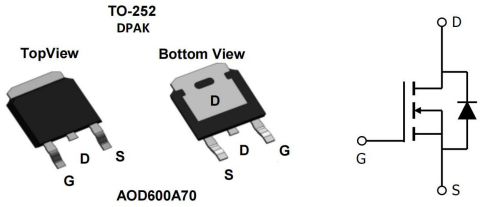
Applications

- Flyback for SMPS
- Charger ,PD Adapter, TV, lighting.

Product Summary

V_{DS} @ $T_{j,max}$	800V
I_{DM}	34A
$R_{DS(ON),max}$	< 0.6Ω
$Q_{g,typ}$	15.5nC
E_{oss} @ 400V	1.8μJ

100% UIS Tested
100% R_g Tested



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOD600A70	TO252	Tape & Reel	2500

Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	±20	V
Gate-Source Voltage (dynamic) AC(f>1Hz)		V_{GS}	±30	V
Continuous Drain Current	T_C=25°C	I_D	8.5	A
	T_C=100°C		5	
Pulsed Drain Current [C]		I_{DM}	34	
Avalanche Current [C] L=1mH		I_{AR}	2.1	A
Repetitive avalanche energy [C]		E_{AR}	2.2	mJ
Single pulsed avalanche energy [G]		E_{AS}	19	mJ
MOSFET dv/dt ruggedness		dv/dt	100	V/ns
Peak diode recovery dv/dt			20	
Power Dissipation [B]	T_C=25°C	P_D	104	W
	Derate above 25°C		0.8	W/°C
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds		T_L	300	°C

Thermal Characteristics

Parameter	Symbol	Typical	Maximum	Units
Maximum Junction-to-Ambient [A,D]	$R_{\theta JA}$	45	55	°C/W
Maximum Case-to-sink [A]	$R_{\theta CS}$	-	0.5	°C/W
Maximum Junction-to-Case [D,F]	$R_{\theta JC}$	1	1.2	°C/W

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Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V, T_J=25°C	700			V
		I_D=250µA, V_{GS}=0V, T_J=150°C		800		
BV_{DSS} /ΔTJ	Breakdown Voltage Temperature Coefficient	I_D=250µA, V_{GS}=0V		0.6		V/ °C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=700V, V_{GS}=0V			1	µA
		V_{DS}=560V, T_J=125°C			10	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±20V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=5V, I_D=250µA	2.9	3.5	4.1	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=2.5A		0.51	0.6	Ω
g_{FS}	Forward Transconductance	V_{DS}=10V, I_D=4A		6.2		S
V_{SD}	Diode Forward Voltage	I_S=4A,V_{GS}=0V		0.86	1.2	V
I_S	Maximum Body-Diode Continuous Current				8.5	A
I_{SM}	Maximum Body-Diode Pulsed Current [C]				34	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		870		pF
C_{oss}	Output Capacitance			23		pF
$C_{o(er)}$	Effective output capacitance, energy related [I]	V_{GS}=0V, V_{DS}=0 to 480V, f=1MHz		20		pF
$C_{o(tr)}$	Effective output capacitance, time related [J]			98		pF
C_{rss}	Reverse Transfer Capacitance	V_{GS}=0V, V_{DS}=100V, f=1MHz		1.3		pF
R_g	Gate resistance	f=1MHz		5		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=480V, I_D=4A		15.5		nC
Q_{gs}	Gate Source Charge			5.6		nC
Q_{gd}	Gate Drain Charge			4.3		nC
$T_{d(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=400V, I_D=4A, R_G=5Ω		22		ns
T_r	Turn-On Rise Time			10		ns
$T_{d(off)}$	Turn-Off DelayTime			36		ns
T_f	Turn-Off Fall Time			8		ns
T_{rr}	Body Diode Reverse Recovery Time	I_F=4A, dI/dt=100A/µs, V_{DS}=400V		245		ns
I_{rm}	Peak Reverse Recovery Current			18.6		A
Q_{rr}	Body Diode Reverse Recovery Charge			3		µC

A. The value of R_{qJA} is measured with the device in a still air environment with T_A=25° C.
B. The power dissipation P_D is based on $T_{J(MAX)}$=150° C in a TO252 package, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.
C. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150° C.
D. The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case R_{qJC} and case to ambient.
E. The static characteristics in Figures 1 to 6 are obtained using <300µs pulses, duty cycle 0.5% max.
F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}$=150° C.
G. L=60mH, I_{AS}=0.8A, R_G=25Ω, Starting T_j=25° C.
H. $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.
I. $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% $V_{(BR)DSS}$.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

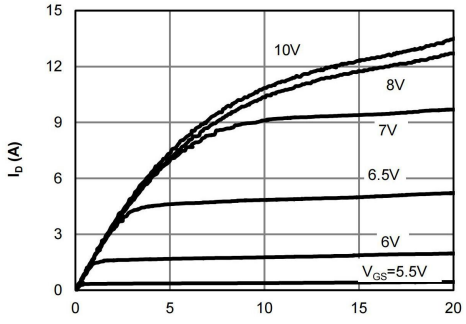


Figure 1: On-Region Characteristics

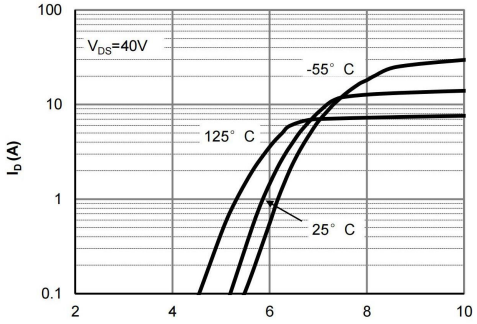


Figure 2: Transfer Characteristics

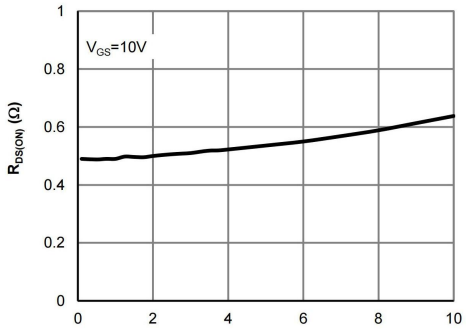


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

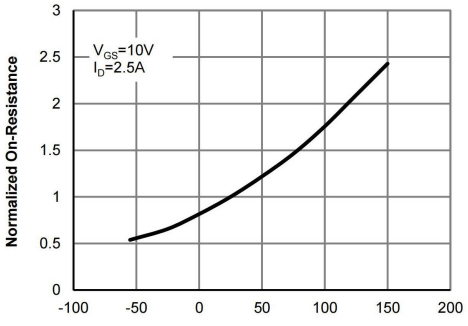


Figure 4: On-Resistance vs. Junction Temperature

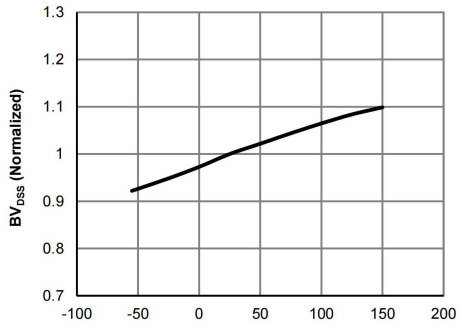


Figure 5: Break Down vs. Junction Temparature

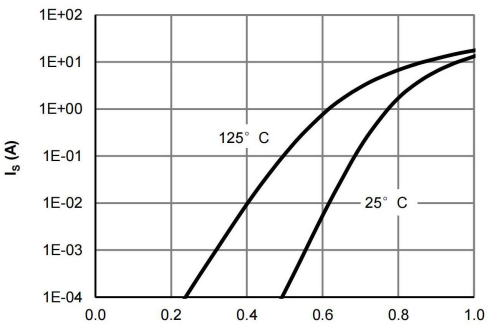


Figure 6: Body-Diode Characteristics

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

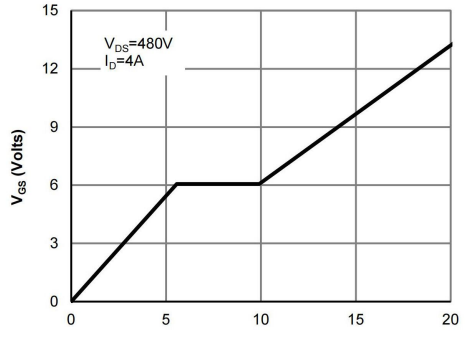


Figure 7: Gate-Charge Characteristics

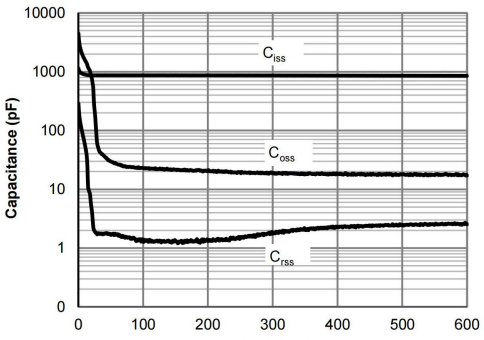


Figure 8: Capacitance Characteristics

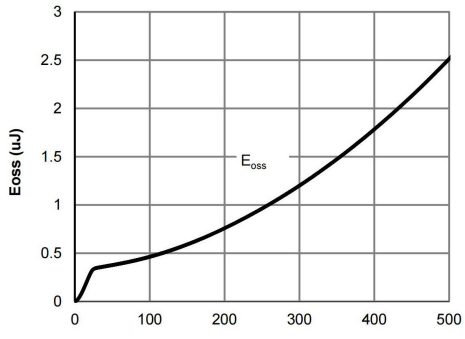


Figure 9: Coss stored Energy

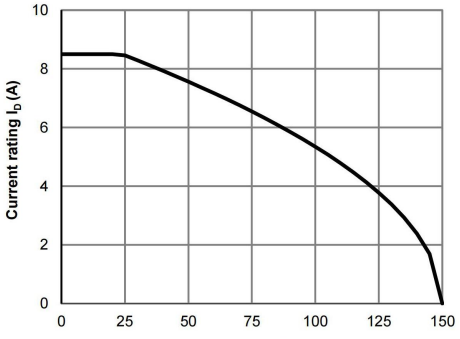


Figure 10: Current De-rating (Note F)

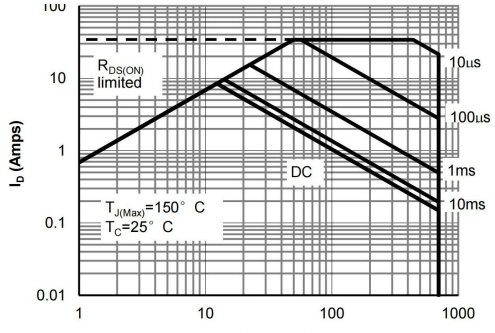


Figure 11: Maximum Forward Biased Safe Operating Area (Note F)

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

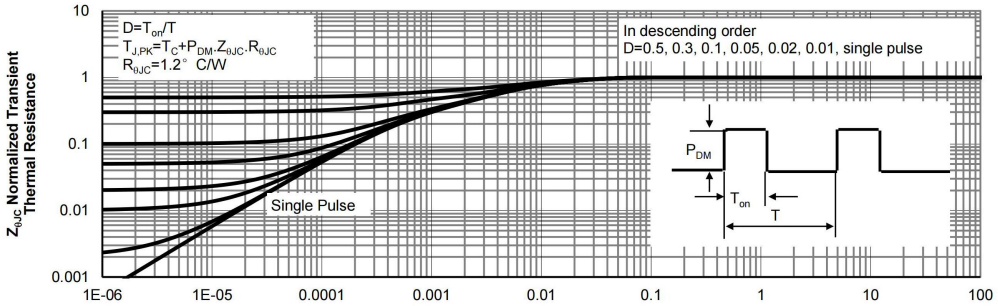
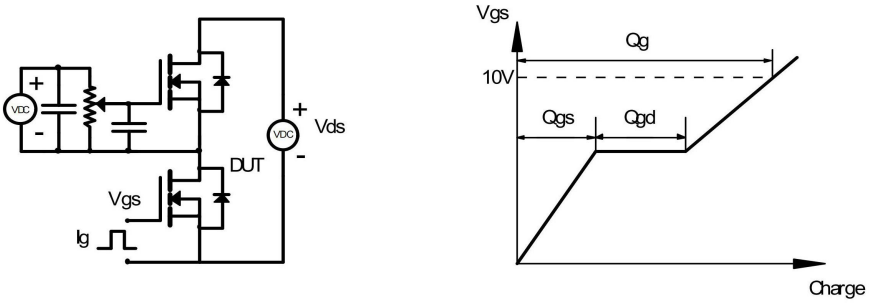


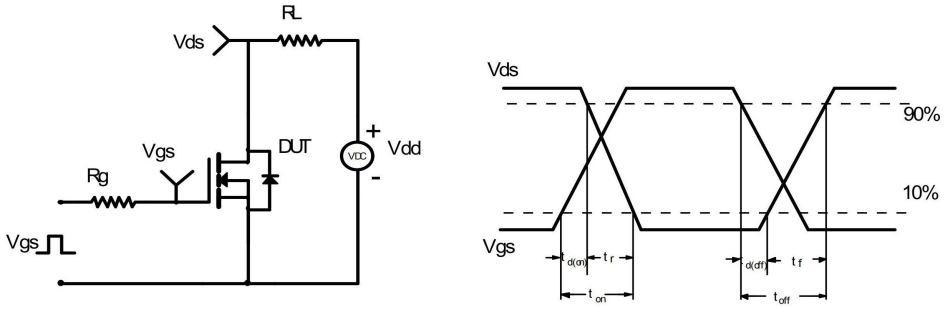
Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)

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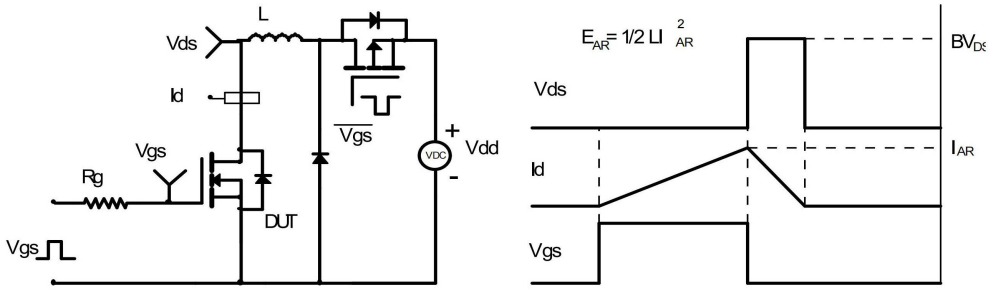
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

